

(Following Paper ID and Roll No. to be filled in your Answer Book)

PAPER ID : 131401

Roll No.

**B.Tech.**

(SEM. IV) THEORY EXAMINATION 2013-14

**ELECTRONIC CIRCUITS***Time : 3 Hours**Total Marks : 100***Note** :- Attempt **all** questions. Each question carries equal marks.

1. Attempt any **four** of the following : (5×4=20)
  - (a) What are the characteristics of the ideal Op Amp ? Explain the concept of Virtual Ground.
  - (b) Design an inverting Op-Amp circuit to form the weighted sum  $v_o$  of two inputs  $v_1$  and  $v_2$ . It is required that  $v_o = -(v_1 + 5 v_2)$ . Choose values for  $R_1$ ,  $R_2$  and  $R_f$  so that for a maximum output voltage of 10 V, the current in the feedback resistor will not exceed 1 mA.
  - (c) Design a noninverting amplifier with a gain of 2 at the maximum output voltage of 10 V the current in the voltage driver is to be 10  $\mu$ A.
  - (d) An enhancement-type NMOS transistor with  $V_t = 0.7$  V conducts a current  $i_D = 100$   $\mu$ A when  $V_{GS} = V_{DS} = 1.2$  V. Find the value of  $i_D$  for  $V_{GS} = 1.5$  V and  $V_{DS} = 3$  V. Also, calculate the value of the drain to source resistance  $r_{DS}$  for a small  $V_{DS}$  and  $V_{GS} = 3.2$  V.

- (e) Explain the operation of enhancement-type N-channel MOSFET as  $V_{DS}$  is increased.
- (f) Consider an n-channel MOSFET with  $t_{ox} = 20$  nm,  $\mu_n = 650$  cm<sup>2</sup>/V-S,  $V_t = 0.8$  V and  $W/L = 10$ . Find the drain current when  $V_{GS} = 5$  V and  $V_{DS} = 1$  V.

2. Attempt any **four** of the following : **(5×4=20)**

- (a) Calculate  $\beta$  for two transistors for which  $\alpha = 0.99$  and  $0.98$ . For collector currents of 10 mA, find the base current of each transistor.
- (b) A BJT having  $\beta = 100$  is biased at a dc collector current of 1 mA. Find the value of  $g_m$ ,  $r_e$  and  $r_\pi$  at the bias point.
- (c) What is the basic principle of Sinusoidal Oscillators ? Explain Barkhausen criterion.
- (d) Explain the properties of Negative Feedback.
- (e) Describe the structure of an npn transistor and explain the operation in the active mode.
- (f) Describe how the performance of an op-amp is affected by the finite open loop gain of amplifier.

3. Attempt any **two** of the following : **(10×2=20)**

- (a) Consider the difference-amplifier circuit of fig. 1. for these cases :  $R_1 = R_3 = 2$  k $\Omega$  and  $R_2 = R_4 = 200$  k $\Omega$ .
- (i) Find the value of differential gain  $A_d$ .
- (ii) Find the value of differential input resistance  $R_{id}$  and the output resistance  $R_o$ .

- (iii) If the resistor has 1% tolerance (i.e. each can be within  $\pm 1\%$  of its nominal value), find the worst-case common mode gain  $A_{cm}$  and the corresponding value of CMRR.

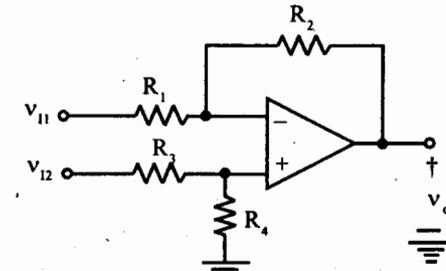


Fig. 1 A Difference Amplifier

- (b) Derive the relation between  $i_D$  and  $V_{DS}$  for NMOS transistor. (Triode region and Saturation region).
- (c) Explain the hybrid- $\pi$  model of the npn transistor.
4. Attempt any **two** of the following : **(10×2=20)**
- (a) Draw the high-frequency hybrid- $\pi$  model and derive an expression for  $h_{fe} \equiv \frac{I_c}{I_b}$ .
- (b) Explain the Four Basic Feedback Topologies.
- (c) Draw the Basic structure of single stage BJT amplifier and find out its characteristic parameters.
5. Explain any **two** of the following : **(10×2=20)**
- (a) Wein-Bridge Oscillator
- (b) MOS differential pair
- (c) Write the disadvantages of RC phase shift oscillator. Draw the circuit diagram of RC phase shift oscillator and derive the expression frequency.